

FIG. 1 Prior Art

FIG. 2

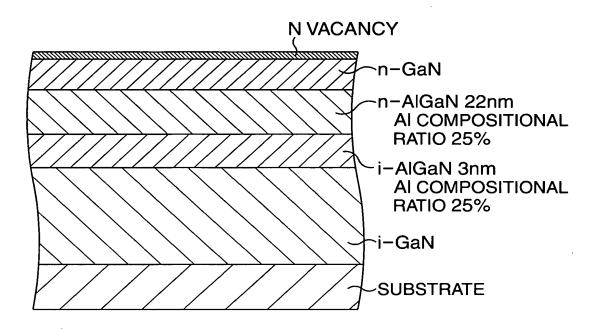


FIG. 3

SURFACE ROUGHNESS (nm)=2.15*x*d (nm)

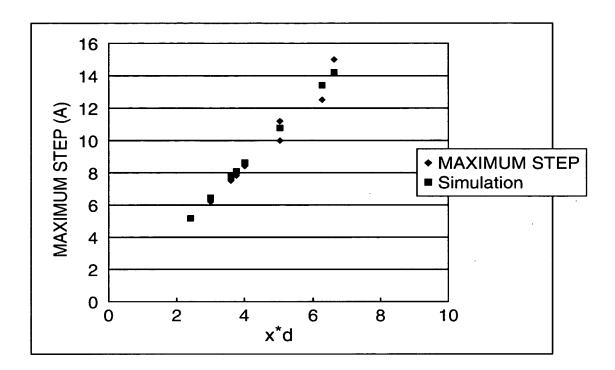


FIG. 4

REVERSE GATE LEAKAGE (μ A/mm) (@Vg=-5V)=1.8E-6*10^ (2.15*x*d*(nm))

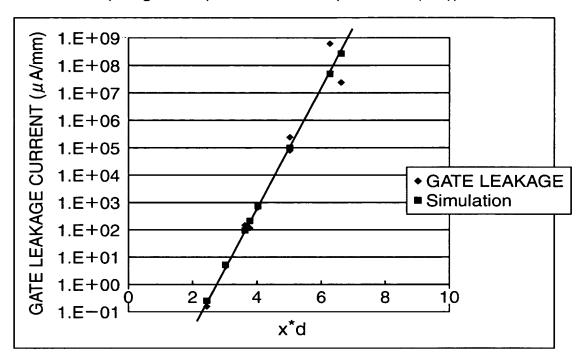
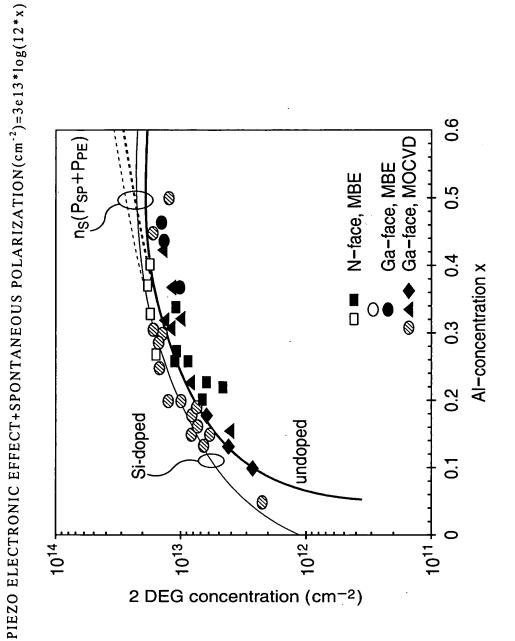
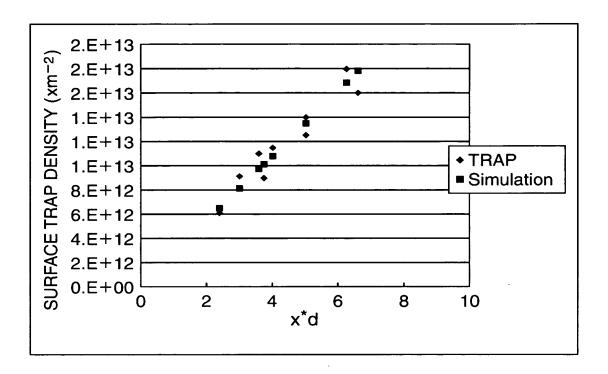


FIG. 5



SURFACE TRAP DENSITY (cm⁻²)=2.7e12* (0.05*x*d*(nm))

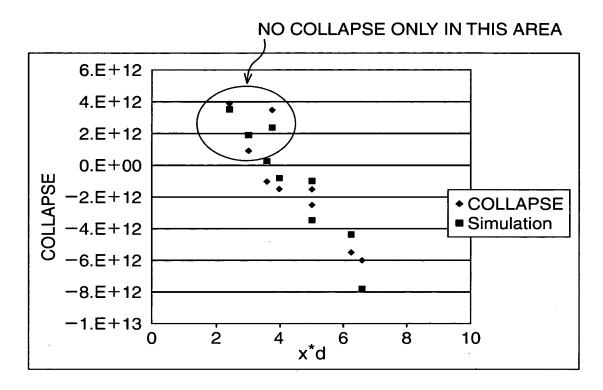
FIG. 6



Title: COMPOUND SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING THE SAME By: Toshihide KIKKAWA Docket No.: 040153

FIG. 7

CURRENT COLLAPSE: 1e-6*Nd*d (nm)/4-2.7e12* (0.05*x*d *(nm))



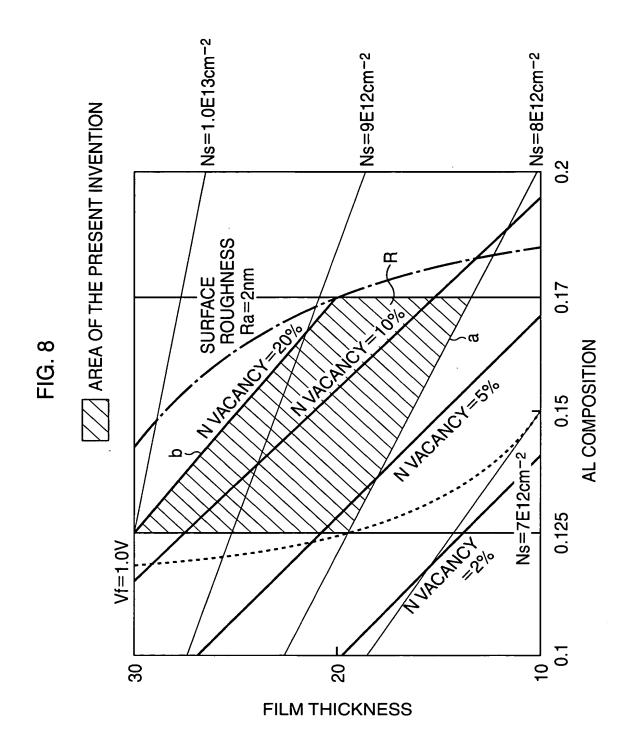
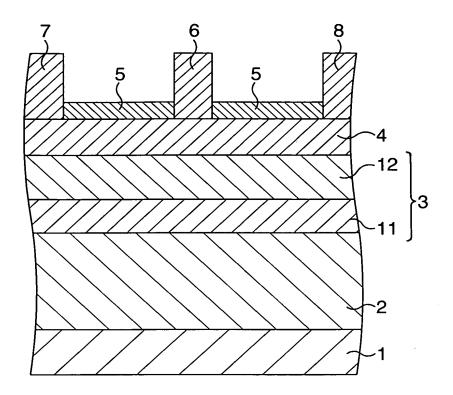
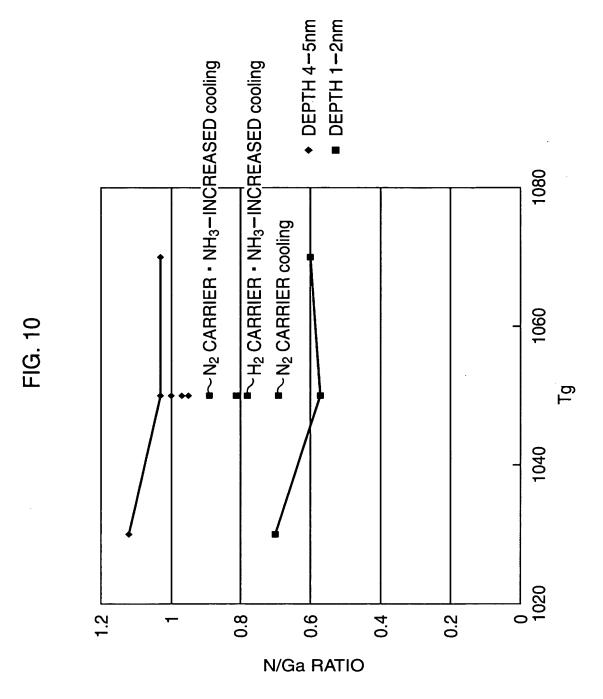


FIG. 9





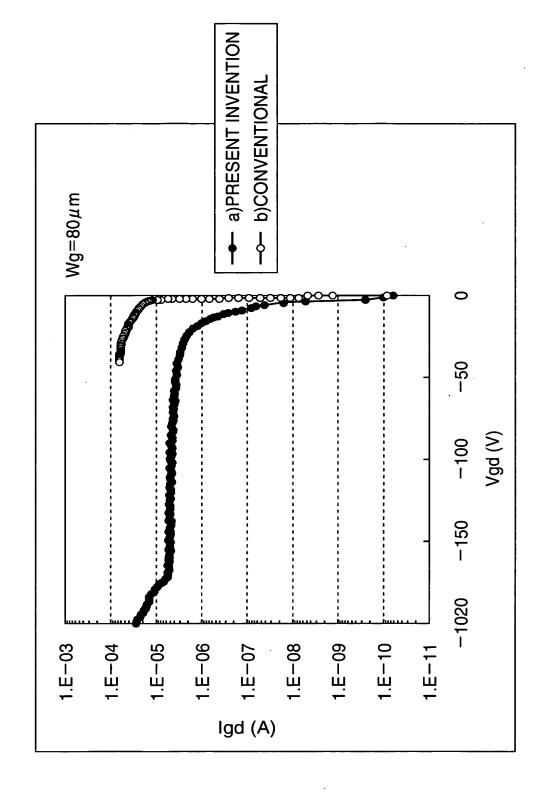


FIG. 11 Prior Art

FIG. 12 Prior Art

